

EAST - [10812590.wsp:1]

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Drafts
Pending
Active
L1: (0) (substrate and (dielectric SiO SiO\$1 silicon near oxide silicon near dioxide insulat\$3) ...
L2: (8) (substrate and (dielectric SiO SiO\$1 silicon near oxide silicon near dioxide insulat\$3) ...
L3: (0) semiconductor near wafer and (SOI silicon near on near insulator) and (substrate and (di
L4: (0) semiconductor near wafer and (SOI silicon near on near insulator) and (substrate and (di
L5: (0) semiconductor near wafer and (SOI silicon near on near insulator) and (nano-crystal nano
L6: (2) wafer and (SOI silicon near on near insulator) and (nano-crystal nano near crystal) and.
L7: (2) substrate and (SOI silicon near on near insulator) and (nano-crystal nano near crystal)..
L8: (2) (SOI silicon near on near insulator) and (nano-crystal nano near crystal) and laser near..
Failed
(0) semiconductor near wafer and (SOI silicon near on near insulator) and (nano-crystal nano ne
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Default operat Highlight all hit terms initially
(substrate and (dielectric SiO SiO\$1 silicon near oxide silicon near dioxide insulat\$3) and crystal and (nano-crystal nano near crystal) and laser near irradiation) and wafer

PDFs HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	R
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040157354 A1	20040812	22	Semiconductor device and method of manufacturing the same	438/45	438/97	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030152867 A1	20030814	73	Information recording medium and its manufacturing method	430/270.13	369/275.2; 369/275.5;	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6762068 B1	20040713	26	Transistor with variable electron affinity gate and methods of fabrication and use	438/16	257/315; 257/323;	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6750471 B2	20040615	12	Molecular memory & logic	257/40	257/24; 257/25;	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6746893 B1	20040608	28	Transistor with variable electron affinity gate and methods of fabrication and use	438/105	438/257; 438/285;	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6554972 B1	20030429	67	Information recording medium and its manufacturing method	204/192.26	204/192.27; 430/270.13;	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6472705 B1	20021029	12	Molecular memory & logic	257/314	257/24; 257/30;	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5926740 A	19990720	12	Graded anti-reflective coating for IC lithography	438/763	257/E21.029; 257/E21.201;	